

DESCRIPTION

The CENTRAL SEMICONDUCTOR CQ220I-16B series type is an Epoxy Molded Silicon Triac designed for full wave AC control applications featuring gate triggering in all four (4) quadrants. This device is mounted in a TO-220 case with an isolated mounting tab.

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

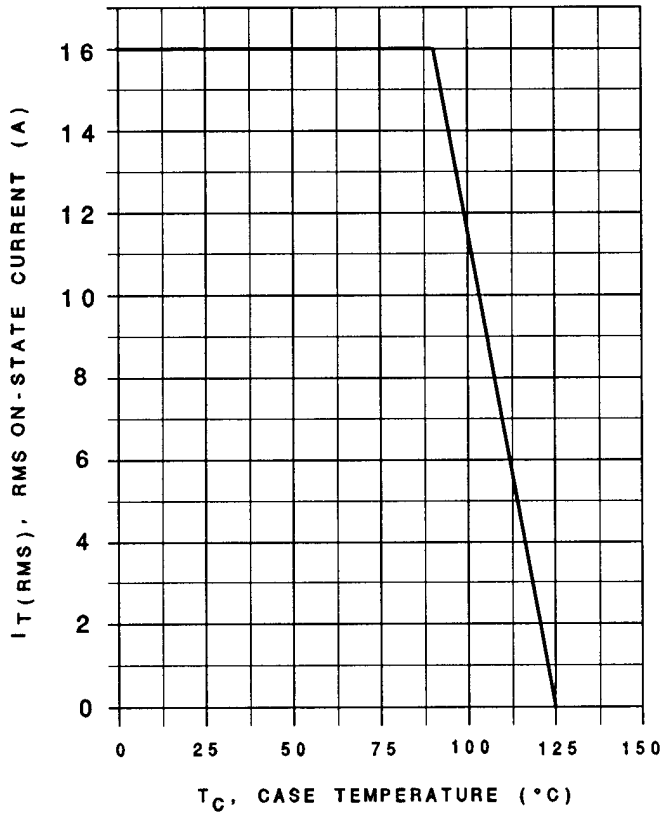
	SYMBOL	CQ220I -16B	CQ220I -16D	CQ220I -16M	CQ220I -16N	UNITS
Peak Repetitive Off-State Voltage	V _{DRM}	200	400	600	800	V
RMS On-State Current (T _C = 90°C)	I _{T(RMS)}			16		A
Peak One Cycle Surge (t = 10ms)	I _{TSM}			170		A
I ² t Value for Fusing (t = 10ms)	I ² t			128		A ² s
Peak Gate Power (tp = 10μs)	P _{GM}			40		W
Average Gate Power Dissipation	P _{G(AV)}			1.0		W
Peak Gate Current (tp = 10μs)	I _{GM}			6.0		A
Peak Gate Voltage (tp = 10μs)	V _{GM}			16		V
Critical Rate of Rise of On-State Current						
Repetitive (F = 50Hz)	di/dt			10		A/μs
Storage Temperature	T _{stg}		-40 to +150			°C
Junction Temperature	T _J		-40 to +125			°C
Thermal Resistance	θ _{J-A}		60			°C/W
Thermal Resistance	θ _{J-C}		2.9			°C/W
Isolation Voltage	V _{ISO}		2500			V _(RMS)

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

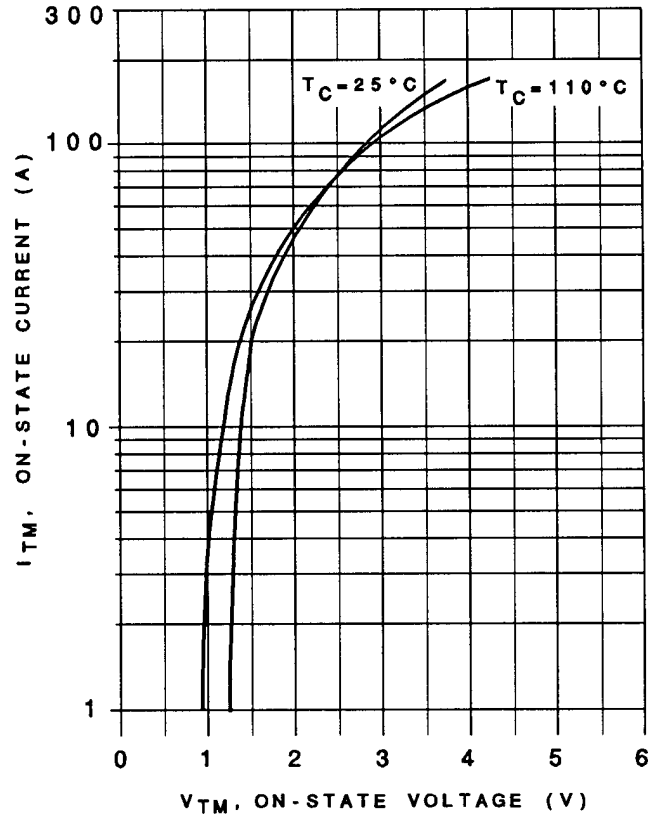
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{DRM}	Rated V _{DRM}			0.01	mA
I _{DRM}	Rated V _{DRM} , T _C = 125°C			2.00	mA
I _{GT}	V _D = 12V, R _L = 33Ω, QUAD I,II,III			50	mA
I _{GT}	V _D = 12V, R _L = 33Ω, QUAD IV			100	mA
I _H	I _T = 100mA			50	mA
V _{GT}	V _D = 12V, R _L = 33Ω, QUAD I,II,III,IV			1.50	V
V _{TM}	I _{TM} = 22.5A, tp = 10ms			1.60	V
dv/dt	V _D = 2/3 V _{DRM} , R _{GK} = ∞, T _C = 125°C	250			V/μs

CQ220I-16B SERIES RATING AND CHARACTERISTIC CURVES

RMS ON-STATE CURRENT vs. CASE TEMPERATURE



MAXIMUM ON-STATE CHARACTERISTICS



MECHANICAL DIMENSIONS

All Dimensions in Inches (mm).

